Morteza Rahimian

List of Publications by Year
in descending order

14	208	1040056 9	1199594 12
papers	citations	h-index	g-index

14	14	14	155
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Improvement of electrical performance in junctionless nanowire TFET using hetero-gate-dielectric. Materials Science in Semiconductor Processing, 2017, 63, 142-152.	4.0	52
2	High-Voltage and RF Performance of SOI MESFET Using Controlled Electric Field Distribution. IEEE Transactions on Electron Devices, 2012, 59, 2842-2845.	3.0	32
3	Leakage current reduction in nanoscale fully-depleted SOI MOSFETs with modified current mechanism. Current Applied Physics, 2012, 12, 1366-1371.	2.4	32
4	Nanoscale SiGe-on-insulator (SGOI) MOSFET with graded doping channel for improving leakage current and hot-carrier degradation. Superlattices and Microstructures, 2011, 50, 667-679.	3.1	22
5	A novel deep submicron SiGe-on-insulator (SGOI) MOSFET with modified channel band energy for electrical performance improvement. Current Applied Physics, 2013, 13, 779-784.	2.4	15
6	A novel nanoscale MOSFET with modified buried layer for improving of AC performance and self-heating effect. Materials Science in Semiconductor Processing, 2012, 15, 445-454.	4.0	14
7	Junctionless nanowire TFET with built-in N-P-N bipolar action: Physics and operational principle. Journal of Applied Physics, 2016, 120, .	2.5	12
8	Dual material insulator SOI-LDMOSFET: A novel device for self-heating effect improvement. Physica E: Low-Dimensional Systems and Nanostructures, 2011, 44, 333-338.	2.7	10
9	Asymmetric junctionless nanowire TFET with built-in $${n}^{+}$$ n + source pocket emphasizing on energy band modification. Journal of Computational Electronics, 2016, 15, 1297-1307.	2.5	9
10	Investigation of the Electrical and Thermal Performance of SOI MOSFETs with Modified Channel Engineering. Materials Science in Semiconductor Processing, 2013, 16, 1248-1256.	4.0	7
11	A novel GaAs MESFET with multi-recessed drift region and partly p-type doped space layer. , 2011, , .		1
12	32 nm high current performance double gate MOSFET for low power CMOS circuits. International Journal of Electronics, 2015, 102, 347-361.	1.4	1
13	Stopped depletion region extension in an AlGaN/GaN-HEMT: A new technique for improving high-frequency performance. Journal of the Korean Physical Society, 2015, 67, 525-532.	0.7	1
14	A novel N-MOSFET with air gaps in gate insulator for deep submicron applications. , 2011, , .		0